

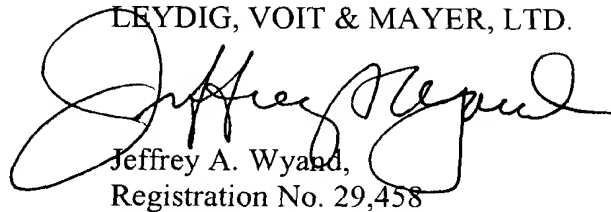
In re Application of Hiroyuki Arakawa
Application No. Unassigned

REMARKS

The foregoing amendments are made to correct minor translational errors and to meet United States requirements as to form. No new matter is added.

Respectfully submitted,

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

HIDEYUKI ARAKAWA

Application No. Unassigned Art Unit: Unassigned

Filed: August 23, 2001 Examiner: Unassigned

For: SEMICONDUCTOR
DEVICE AND
MANUFACTURING
METHOD THEREOF

AMENDMENTS TO SPECIFICATION, CLAIMS, AND
ABSTRACT MADE VIA PRELIMINARY AMENDMENT

Amendments to the paragraph beginning at page 1, line 20:

When a reverse loop such as shown in Fig. 8 is utilized, an inner lead 10 and a bonding pad 6 are connected by means of a first ball 2, a bonding wire 1, and a stud bump (second ball) 9. Bonding pad 6 is formed on a semiconductor device (chip) 7 mounted on a die pad 8.

Amendments to the paragraph beginning at page 1, line 24:

When a chip-to-chip loop such as shown in Fig. 9 is utilized, bonding pads 6 ~~formed~~ on semiconductor device 7 are connected to each other by means of first ball 2, the bonding wire 1, and stud bump (second ball) 9.

Amendments to the paragraph beginning at page 1, line 27:

In the reverse loop or chip-to-chip technique, secondary bonding is performed on the bonding pad 6 on the chip. Here, a stud ~~bumps~~ bump 9 is formed in advance on bonding pad 6 as shown in Fig. 10, and the secondary bonding is performed on stud bump 9, using a capillary 4 and a wire cut clammer 5 as shown in Fig. 11. Namely, an on-bump

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secondary bonding technique is used. In the on-bump secondary bonding technique, the step of arranging a stud bump is necessary, separate from the step of arranging the wire. This results in larger number of steps required for wire bonding, resulting in low efficiency in manufacturing the semiconductor devices.

Amendments to the paragraph beginning at page 5, line 27:

Fig. 6 is a side view showing a characteristic step of manufacturing ~~the~~ a semiconductor device in accordance with a second embodiment of the present invention.

Amendments to the paragraph beginning at page 6, line 4:

Fig. 9 is a cross sectional view showing another example (chip-to-chip loop) of ~~the~~ a conventional method of wire connection.

Amendments to the existing claims:

1. (Amended) A semiconductor device, comprising:
a first conductive layer;
a first ball ~~formed~~ on said first conductive layer;
a second conductive layer ~~arranged~~ spaced apart from said first conductive layer;
a second ball ~~formed~~ on said second conductive layer; and
a bonding wire connecting said first and second balls, wherein said second ball is formed by mechanically deforming said bonding wire.

2. (Amended) The semiconductor device according to claim 1, wherein said second ball is formed by bending said bonding wire on said second conductive layer.

3. (Amended) The semiconductor device according to claim 1, wherein said second ball is formed by making curving said bonding wire ~~curved~~ on said second conductive layer.

5. (Amended) The semiconductor device according to claim 1, comprising
a base;
a semiconductor element ~~formed~~ on said base with a die pad interposed between
said semiconductor element and said base;
a sealing resin sealing said semiconductor element; and
an external terminal ~~formed~~ on a rear surface of said base, wherein
said first conductive layer includes a land ~~formed~~ on said base, and
said second conductive layer includes a bonding pad ~~formed~~ on said
semiconductor element.

6. (Amended) The semiconductor device according to claim 1, comprising:
a base;
first and second semiconductor elements mounted on said base with a die pad
interposed between said base and said first and second semiconductor elements;
a sealing resin sealing said first and second semiconductor elements; and
an external terminal ~~formed~~ on a rear surface of said base, wherein
said first conductive layer includes a first bonding pad ~~formed~~ on said first
semiconductor element, and
said second conductive layer includes a second bonding pad ~~formed~~ on said
second semiconductor element.

7. (Amended) A method of manufacturing a semiconductor device, comprising,
sequentially:
~~a first bonding step of~~ joining a first ball formed at a tip end of a bonding wire to a
first conductive layer;
~~after said first bonding step,~~ joining said bonding wire to a second conductive
layer;
mechanically deforming said bonding wire on said second conductive layer, with
said bonding wire joined to the second conductive layer; and
~~a second bonding step of~~ joining the ~~deformed~~ portion of said bonding wire
deformed to said second conductive layer.

8. (Amended) The method of manufacturing a semiconductor device according to claim 7, wherein ~~said step of~~ mechanically deforming said bonding wire includes ~~the step of~~ bending said bonding wire on said second conductive layer.

9. (Amended) The method of manufacturing a semiconductor device according to claim 7, wherein ~~said step of~~ mechanically deforming said bonding wire includes ~~the step of making curving~~ said bonding wire ~~curved~~ on said second conductive layer.

10. (Amended) The method of manufacturing a semiconductor device according to claim 7, wherein

said bonding wire is held by a bonding tool; and

~~said step of~~ mechanically deforming said bonding wire includes ~~the step of~~ mechanically deforming said bonding wire on said second conductive layer by moving said bonding tool with said bonding wire being joined to said second conductive layer.

Amendments to the abstract:

ABSTRACT OF THE DISCLOSURE

A semiconductor device ~~of the present invention~~ includes an inner lead, a first ball ~~formed~~ on the inner lead, a bonding pad ~~formed on a~~ the semiconductor device, a second ball ~~formed~~ on the bonding pad, and a bonding wire connecting the first and second balls. The second ball is formed by mechanically deforming the bonding wire.

In re Application of:

Application No. Unassigned Art Unit: Unassigned

Filed: August 23, 2001 Examiner: Unassigned

PENDING CLAIMS AFTER ENTRY OF PRELIMINARY AMENDMENT

1. A semiconductor device, comprising:
a first conductive layer;
a first ball on said first conductive layer;
a second conductive layer spaced apart from said first conductive layer;
a second ball on said second conductive layer; and
a bonding wire connecting said first and second balls, wherein said second ball is formed by mechanically deforming said bonding wire.
2. The semiconductor device according to claim 1, wherein said second ball is formed by bending said bonding wire on said second conductive layer.
3. The semiconductor device according to claim 1, wherein said second ball is formed by curving said bonding wire on said second conductive layer.
4. The semiconductor device according to claim 1, wherein
said first conductive layer includes an inner lead; and
said second conductive layer includes a bonding pad.

5. The semiconductor device according to claim 1, comprising
a base;
a semiconductor element on said base with a die pad interposed between said semiconductor element and said base;
a sealing resin sealing said semiconductor element; and
an external terminal on a rear surface of said base, wherein
said first conductive layer includes a land on said base, and
said second conductive layer includes a bonding pad on said semiconductor element.

6. The semiconductor device according to claim 1, comprising:
a base;
first and second semiconductor elements mounted on said base with a die pad interposed between said base and said first and second semiconductor elements;
a sealing resin sealing said first and second semiconductor elements; and
an external terminal on a rear surface of said base, wherein
said first conductive layer includes a first bonding pad on said first semiconductor element, and
said second conductive layer includes a second bonding pad on said second semiconductor element.

7. A method of manufacturing a semiconductor device, comprising, sequentially:
joining a first ball formed at a tip end of a bonding wire to a first conductive layer;
joining said bonding wire to a second conductive layer;
mechanically deforming said bonding wire on said second conductive layer, with said bonding wire joined to the second conductive layer; and
joining the portion of said bonding wire deformed to said second conductive layer.

8. The method of manufacturing a semiconductor device according to claim 7, wherein mechanically deforming said bonding wire includes bending said bonding wire on said second conductive layer.

9. The method of manufacturing a semiconductor device according to claim 7, wherein mechanically deforming said bonding wire includes curving said bonding wire on said second conductive layer.

10. The method of manufacturing a semiconductor device according to claim 7, wherein

said bonding wire is held by a bonding tool; and

mechanically deforming said bonding wire includes mechanically deforming said bonding wire on said second conductive layer by moving said bonding tool with said bonding wire being joined to said second con

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